



Part Number :		Date:	7 February 2005
Customer:		STD:	Y
Customer Specification/ Reference:			

Category	Parameter	Specification	Measurement Method
<i>Overall</i>			
<i>Wafer</i>			
1.1	Diameter	150mm +/- 0.5	Wafer Vendor
1.2	Primary Flat Orientation	{110}+/- 1°	Wafer Vendor
1.3	Primary Flat Length	47.5mm +/-2.5	Wafer Vendor
1.4	Secondary Flat Orientation	None	
1.5	Thickness	629 µm +/- 6	Guaranteed by Process
1.6	Total Thickness Variation(TTV)	< 5µm	Guaranteed by Process
1.7	Bow	< 50 um	ADE to ASTM F534, 20%
1.8	Warp	< 50um	ADE to ASTM F657, 20%
1.9	Edge Chips	0	Bright Light, 100% ¹
1.10	Edge Exclusion	5mm	
<i>Handle</i>			
<i>Silicon</i>			
2.1	Growth Method	CZ/FZ	Wafer Vendor
2.2	Orientation	{100}+/- 1°	Wafer Vendor
2.3	Thickness	525µm +/- 5µm	ADE, 100%
2.4	Doping type	N	Wafer Vendor
2.5	Dopant	Phosporous	Wafer Vendor
2.6	Resistivity	1 – 10 ohm-cm	Wafer Vendor
2.7	Backside Finish	Polished with oxide & lasermark ID	Guaranteed by Process
<i>Buried</i>			
<i>Oxide</i>			
3.1	Oxide Type	Thermal	
3.2	Oxide Thickness	4000 nm +/- 200nm	Nanospec centre point, 4%
3.3	Oxide formed on	Handle Wafer	

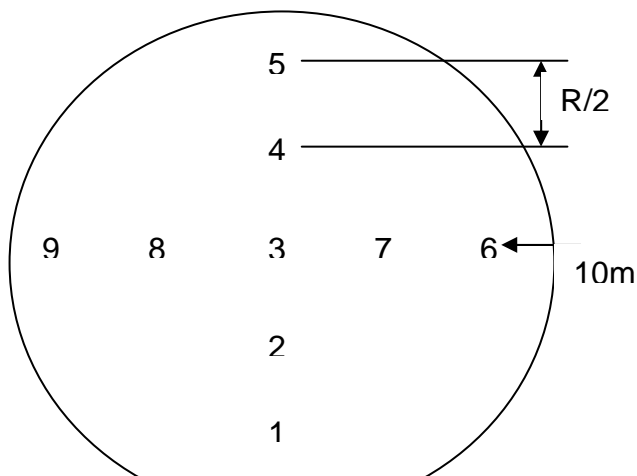
Category	Parameter	Specification	Measurement Method
<i>Device</i>			
<i>Silicon</i>			
4.1	Growth Method	FZ	Wafer Vendor
4.2	Orientation	{100}+/- 1°	Wafer Vendor
4.3	Nominal Thickness	100 µm	FTIR / ADE, 100%
4.4	Thickness Variation	+/- 0.5 µm	FTIR/ ADE, 100% 9 point
4.5	Distance to device silicon		
	edge from wafer edge	<5mm	Typical by process
4.6	Doping Type	N	Wafer Vendor
4.7	Dopant	Phosphorous	Wafer Vendor
4.8	Resistivity	>4000 ohm-cm	Wafer Vendor
4.9	Voids	0	Bright Light, 100% ¹
4.10	Scratches	0	Bright Light, 100% ¹
4.11	Haze	None	Bright Light, 100% ¹
4.12	Particles	<30 @0.3um	Tencor 6220

Shipping Details

Wafers per box	25 max
Packaging	Taped Polypropylene Wafer Box Empak, Ultrapak, 150mm Antistatic Double Bagging
Lot Shipment Data :	Device Silicon Thickness Handle Wafer Thickness SOI wafer thickness, TTV SOI wafer Bow/Warp

Explanatory Notes

1. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in 1.10. High intensity bright lamp inspection as per ASTM F523.
2. 9 point measurement is centre and 4 points 10mm from edge of wafer.



Approvals:	Quality:	Engineering:
	Marketing:	TRB:

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